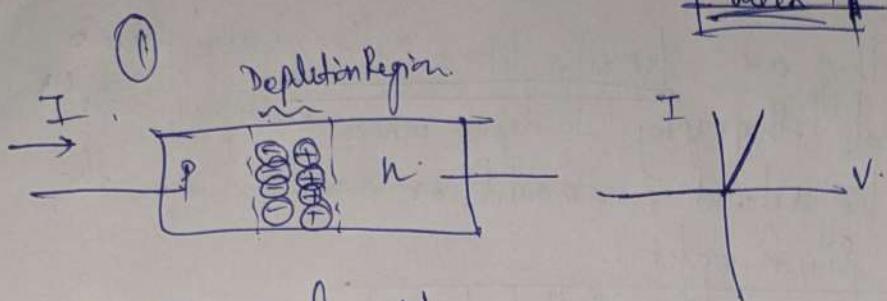


# Semiconductor Fabrication - 101

Week 1



① Tap Analogy !!

(Mosfet as a switch)

('defect free base').

② Microfab :-

Starting material : Single crystal silicon - extremely pure.

Mask Set :

Process Sequence :-

gives  $\geq$  direct info.

defines x-y patterns that will be transferred onto silicon.

each mask corresponds to one lithography & step in the process.

shows how layers are built, etched or deposited step by step in depth.

③ Counter doping :- introducing impurities of opposite type  
(e.g. n-type into p-type)

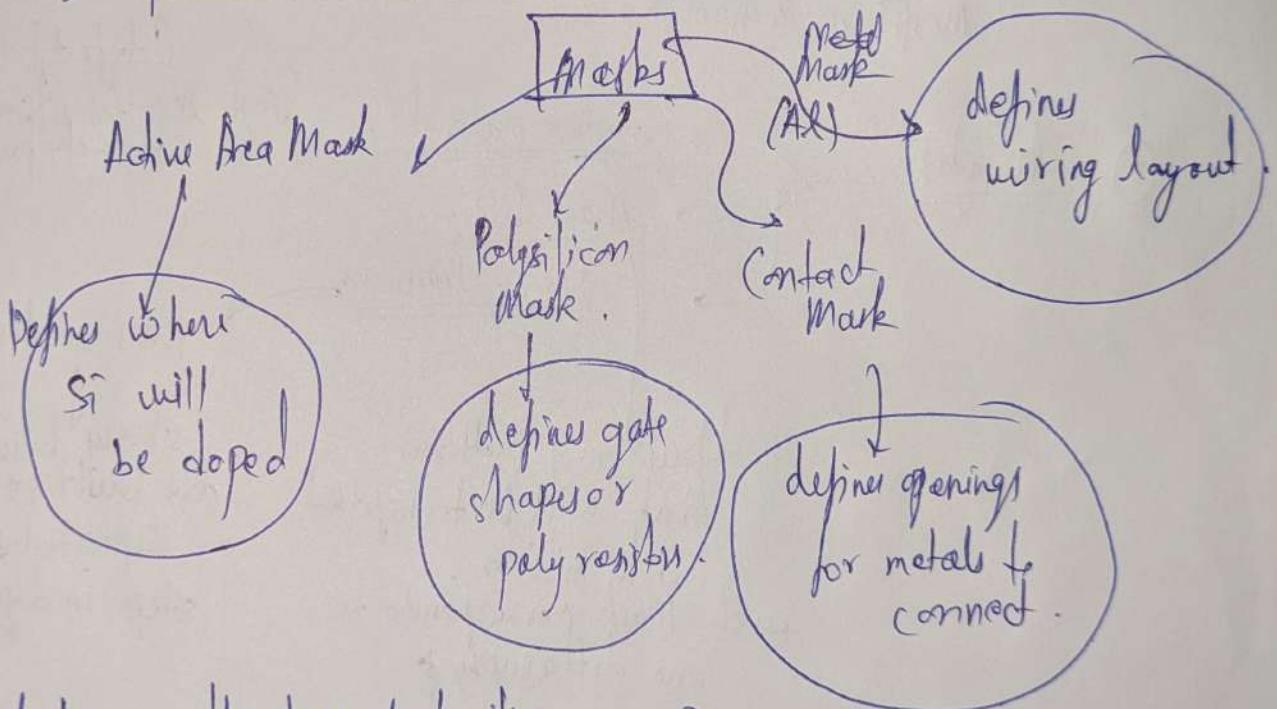
→ ~~you~~ one might use it to compensate for unintended doping!

④ Annealing → the heat treatment ~~used~~ for materials that soften them, reduces hardness & increases ductility by heating, holding & then cooling the material. This reorganizes the material's internal structure, easier to work with.

~~Mask~~

~~Mask~~: - They are stencil-like patterns used during photolithography to define which material should be added, removed or modified on the silicon wafer.

~~Each mask~~: - one layer of that device



What exactly does polysilicon mean?

- Polycrystalline Silicon.
- Small randomly oriented crystals fused together, contrasting with single-crystal silicon (monocrystalline).
- Extremely high purity.

→ Chip fabrication is like drawing shapes layer by layer on wafer

6-inch si wafer lightly doped  
n-type.

Heating wafers in  $O_2$  so that oxide forms  
on top.

Expose Si  
only in place  
where transistors  
exist, everywhere  
else → covered  
by oxide

Pattern Active Area (Mask 1)  
(Coat, expose, develop, etch) green area  
place mask | etch  
UV through mask, → those places photresist is soluble  
place mask | Photresist washed away since soluble! wanted  
etch | etch  
etch gate oxide

sinter  
↑  
Pattern Al (Mask 4)

↑  
evaporate  
Al

Deposit Polysilicon  
Pattern Polysilicon (Mask 2)

Etch gate oxide

Implant Boron

Dope in

strip Backside

(Mask 3).  
Pattern Contact Cuts

Green :- for transistors

Red : make the gate

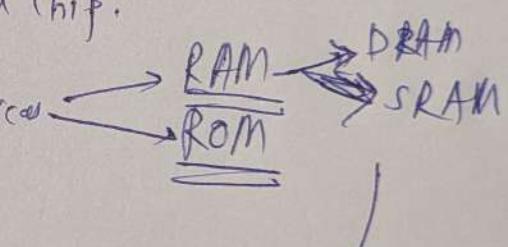
Ton implement'n :- make source / drain aligned to gate

Black :- open holes for connection

Blue :- metal wiring later connects everything

with just 4 marks  $\rightarrow$  the fab process can create all fundamental circuit components: resistors, caps, diodes, Mosfet & even BJTs!

## TEL Keypoints (General Reading material)

- ① CN: Carbon Nanotube → diameter: nanoscale.  
can be single walled or even "nested" multi-walled.  
→ exceptional tensile strength & thermal conductivity.
- ② Integrated IC: combines all parts onto a single substrate or chip.
- ③ Kilby's groundbreaking idea! : father of IC in a way.  
@ (TI)
- ④ Moore's Law: - no. of transistors will double every 18 months.
- ⑤ Microprocessor: - CPU ~~on~~ on a Chip.
- ⑥ Semiconductor memory devices  
  
I have already spent hours on these concepts while studying for NC

## ⑦ Liquid crystal (New)!

→ ~~solid~~ properties of both solids & liquids.

→ Cholesteryl benzoate (Flowing crystal) → (liquid crystal)  
Notes! → melting pts ( $M_P^1$  &  $M_P^2$ ) & in blue fluorescence

anisotropy (optical property)

As you apply voltage (change voltage)  $\rightarrow$  orientation of LC molecules changes  
(transparency changes)

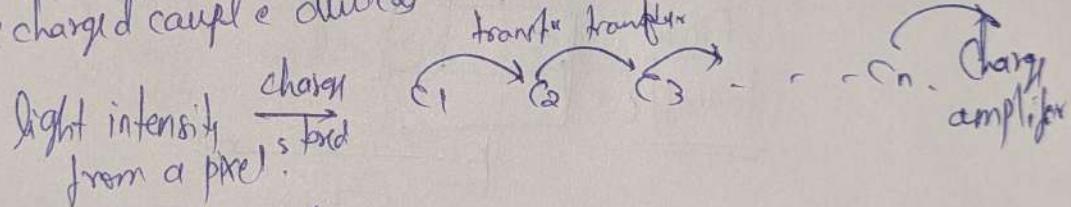
Thin film transistors (compos<sup>n</sup> from amorphous silicon)

used to make LCD (Liquid Crystal Displays)

{ TFTs are special kinds of FETs made by thin film depos<sup>n</sup> process  
substrate  $\rightarrow$  generally glass. { unlike mosfet in which substrate  $\rightarrow$  si wafer }

④ Image Sensors (2 kinds mentioned)

CCDs: charged couple devices



(mos sensors use less power than CCD ones -

↓ large circuitry on smaller areas (also lower cost)!

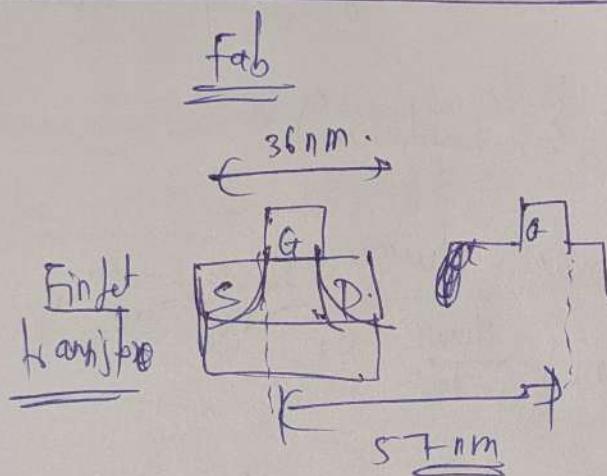
④ GaAs: - only a goat but Si wins because lesser expensive!

Doping

$n^-, p^- \rightarrow$  light doping  
 $n^-, p \rightarrow$  Normal Doping  
 $n^+, p^+ \rightarrow$  Heavy Doping

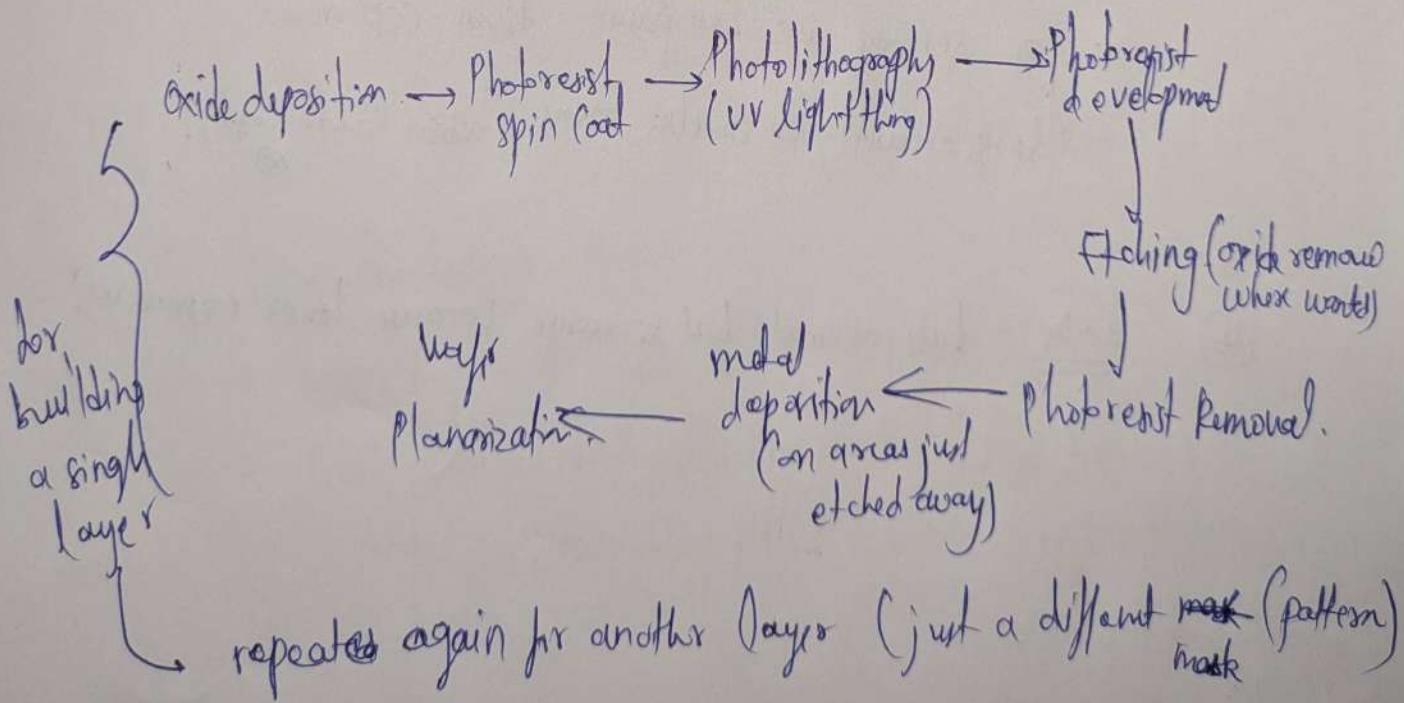
- ① Ion Implantation \* Followed by  
 ② Wafer growth doping.  
 ③ Diffusion

Methods of Doping



Clean room

Die  $\rightarrow$  Another name for chip?

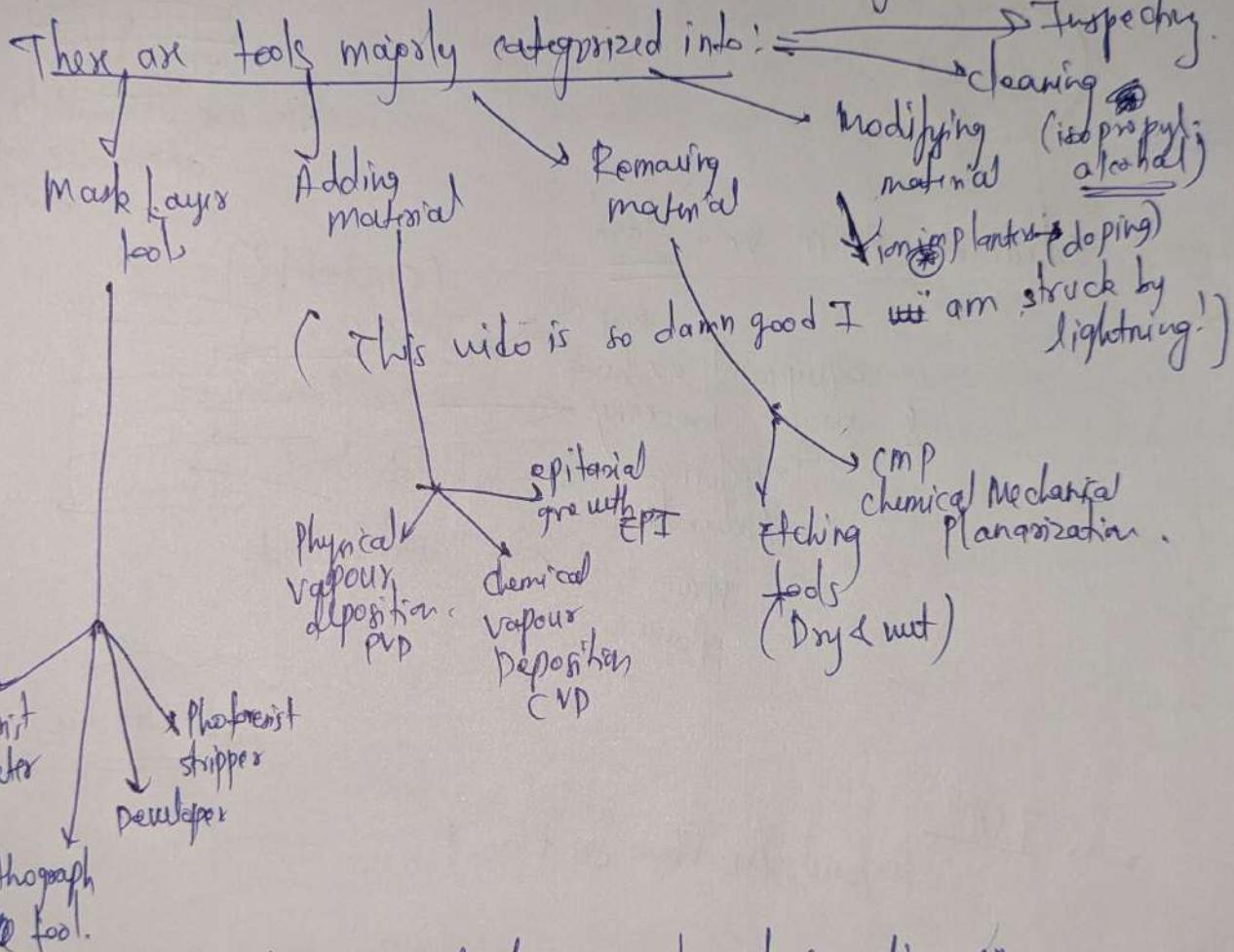


FOUP - Front Opening Universal Pod

→ carries silicon wafers in batcher/grips  
of ~25 (say)

(3 months of travelling of FOUP from tool to tool)  
(almost) in a fab.

scanning  
e-microscope



Semiconductor industry: extremely secretive ☺

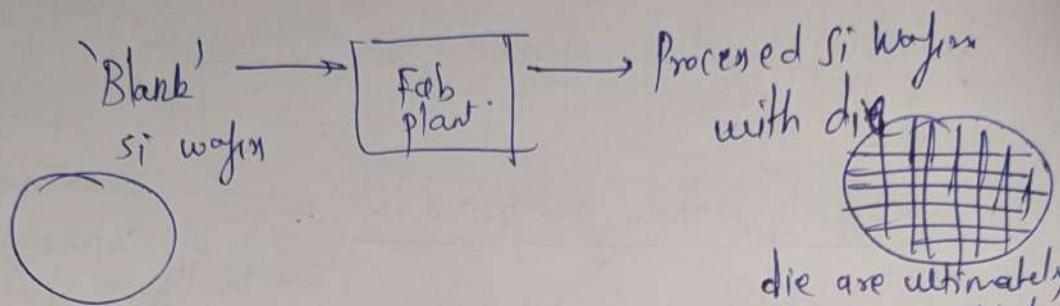
Note:- Nutology device

(Inspectory devices)

like diagnosis (not useful)

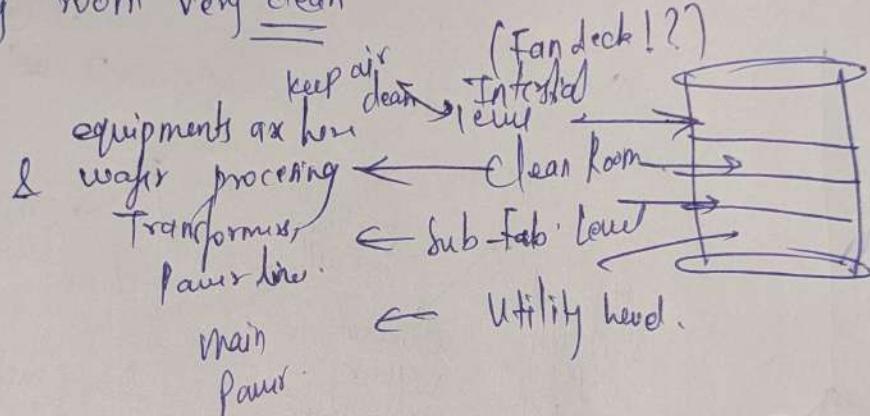
just give confidence  
to stay & keep moving.

Semi X Talk Lec ~~on~~ on Fab functioning  
 Tata's → fab plant in Gujarat!



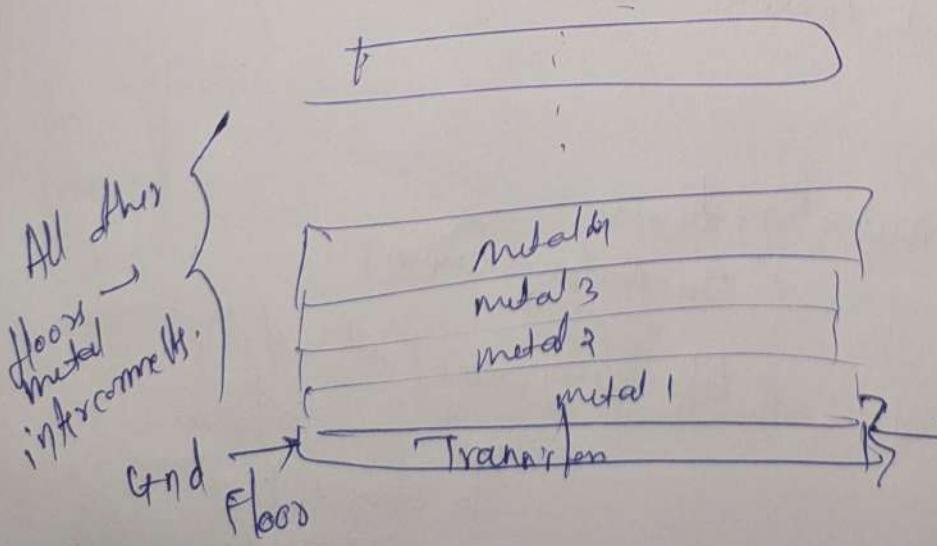
die are ultimately assembled as chips.

Cleaning room very 'clean'

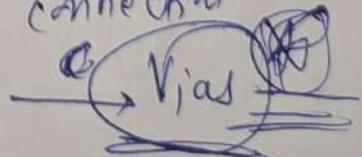


Fab Structure

→ ISM<sup>c</sup> Perforated Air Flow at Flow!



metal to metal connection



Metal 1 to transistor connection (contacts)

## Wafer & Feature size

As wafer size ↑ : economic boom (you'll get  $\frac{5}{2.25}$  times more chips per wafer)

## Understandable

1976  
100 mm

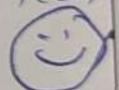
1983  
150 mm

1992  
200 mm

2001  
300 mm

After 2001 hasn't led to

Feature size - The minimum dimension of a transistor that can be manufactured on a chip. The lesser it is more advanced the tech



Tata → will be capable of 28 nm

Chip war :- Chris Miller

Do Read !!

failing fast! better! & changing path & doing the right thing!

 fundamentally understand semiconductors & then become an Entrepreneur!